



STGB8NC60K - STGD8NC60K STGP8NC60K

N-channel 600V - 8A - D²PAK / DPAK / TO-220
Short circuit rated PowerMESH™ IGBT

Features

Type	V _{CES}	V _{CE(sat)} Typ @ 25°C	I _C @ 100°C
STGB8NC60K	600V	2.2V	8A
STGD8NC60K	600V	2.2V	8A
STGP8NC60K	600V	2.2V	8A

- Lower on voltage drop (V_{cesat})
- Lower C_{RES} / C_{IES} ratio (no cross-conduction susceptibility)
- Very soft ultra fast recovery antiparallel diode
- Short circuit withstand time 10μs

Applications

- High frequency motor controls
- SMPS and PFC in both hard switch and resonant topologies
- Motor drivers

Description

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The suffix "K" identifies a family optimized for high frequency motor control applications with short circuit withstand capability.

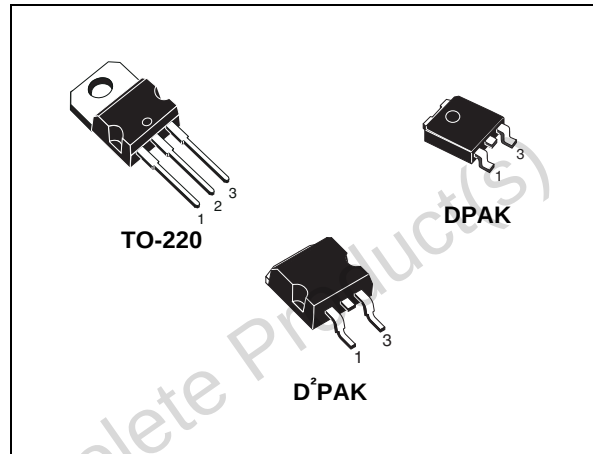


Figure 1. Internal schematic diagram

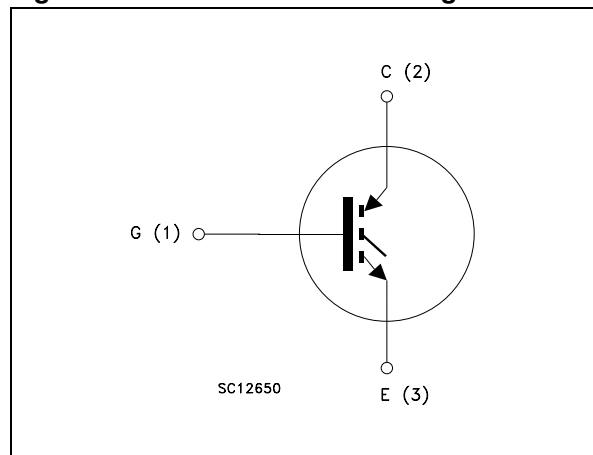


Table 1. Device summary

Order codes	Marking	Package	Packaging
STGB8NC60K	GB8NC60K	D ² PAK	Tape & reel
STGD8NC60K	GD8NC60K	DPAK	Tape & reel
STGP8NC60K	GP8NC60K	TO-220	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		D ² PAK/TO-220	DPAK	
V _{CES}	Collector-emitter voltage (V _{GS} = 0)	600		V
I _C ⁽¹⁾	Collector current (continuous) at T _C = 25°C	15		A
I _C ⁽¹⁾	Collector current (continuous) at T _C = 100°C	8		A
I _{CP} ⁽²⁾	Pulsed collector current	30		A
V _{GE}	Gate-emitter voltage	±20		V
P _{TOT}	Total dissipation at T _C = 25°C	65	62	W
T _j	Operating junction temperature	– 55 to 150		°C
T _{scw}	Short circuit withstand time	10		µs

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_C, I_C)}$$

2. Pulse width limited by max junction temperature

Table 3. Thermal resistance

Symbol	Parameter		Value	Unit
R _{thj-case}	Thermal resistance junction-case max	TO-220 / D ² PAK	1.9	°C/W
		DPAK	2.0	°C/W
R _{thj-amb}	Thermal resistance junction-ambient Max		62.5	°C/W

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{BR(CES)}$	Collector-emitter breakdown voltage	$I_C = 1\text{mA}$, $V_{GE} = 0$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{V}$, $I_C = 3\text{A}$ $V_{GE} = 15\text{V}$, $I_C = 3\text{A}$, $T_C = 125^{\circ}\text{C}$		2.2 1.8	2.75	V V
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 250\text{ }\mu\text{A}$	4.5		6.5	V
I_{CES}	Collector cut-off current ($V_{GE} = 0$)	$V_{CE} = \text{Max rating}$, $T_C = 25^{\circ}\text{C}$ $V_{CE} = \text{Max rating}$, $T_C = 125^{\circ}\text{C}$			150 1	μA mA
I_{GES}	Gate-emitter leakage current ($V_{CE} = 0$)	$V_{GE} = \pm 20\text{V}$, $V_{CE} = 0$			± 100	nA
g_{fs}	Forward transconductance	$V_{CE} = 15\text{V}$, $I_C = 3\text{A}$		15		S

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{V}$, $f = 1\text{MHz}$, $V_{GE} = 0$		380		pF
C_{oes}	Output capacitance			46		pF
C_{res}	Reverse transfer capacitance			8.5		pF
Q_g	Total gate charge	$V_{CE} = 390\text{V}$, $I_C = 3\text{A}$,		19		nC
Q_{ge}	Gate-emitter charge	$V_{GE} = 15\text{V}$,		5		nC
Q_{gc}	Gate-collector charge	(see Figure 18)		9		nC

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 390V$, $I_C = 3A$ $R_G = 10\Omega$, $V_{GE} = 15V$, $T_J = 25^\circ C$ (see Figure 19)		17 6 655		ns ns A/ μs
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 390V$, $I_C = 3A$ $R_G = 10\Omega$, $V_{GE} = 15V$, $T_J = 125^\circ C$ (see Figure 19)		16.5 6.5 575		ns ns A/ μs
$t_r(V_{off})$ $t_{d(off)}$ t_f	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 390V$, $I_C = 3A$, $R_{GE} = 10\Omega$, $V_{GE} = 15V$, $T_J = 25^\circ C$ (see Figure 19)		33 72 82		ns ns ns
$t_r(V_{off})$ $t_{d(off)}$ t_f	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 390V$, $I_C = 3A$, $R_{GE} = 10\Omega$, $V_{GE} = 15V$, $T_J = 125^\circ C$ (see Figure 19)		60 106 136		ns ns ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{on}^{(1)}$ $E_{off}^{(2)}$ E_{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 390V$, $I_C = 3A$ $R_G = 10\Omega$, $V_{GE} = 15V$, $T_J = 25^\circ C$ (see Figure 19)		55 85 140		μJ μJ μJ
$E_{on}^{(1)}$ $E_{off}^{(2)}$ E_{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 390V$, $I_C = 3A$ $R_G = 10\Omega$, $V_{GE} = 15V$, $T_J = 125^\circ C$ (see Figure 19)		87 162 249		μJ μJ μJ

1. E_{on} is the turn-on losses when a typical diode is used in the test circuit in figure 2. If the IGBT is offered in a package with a co-pak diode, the co-pak diode is used as external diode. IGBTs & Diode are at the same temperature ($25^\circ C$ and $125^\circ C$)
2. Turn-off losses include also the tail of the collector current

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

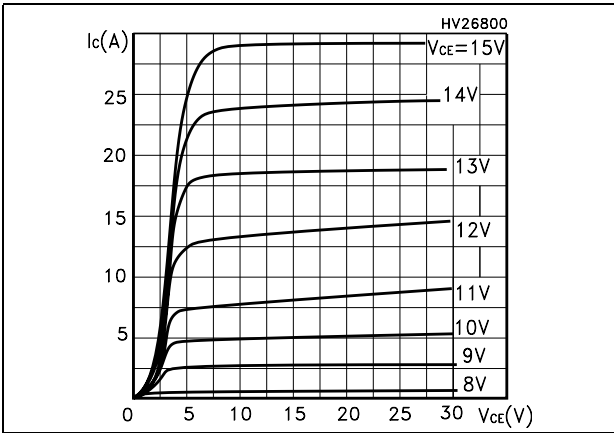


Figure 3. Transfer characteristics

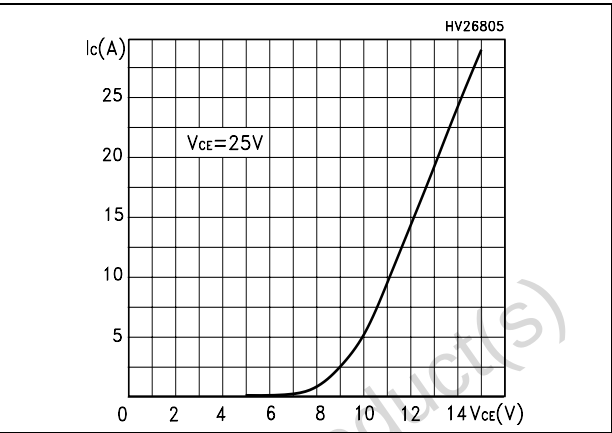


Figure 4. Transconductance

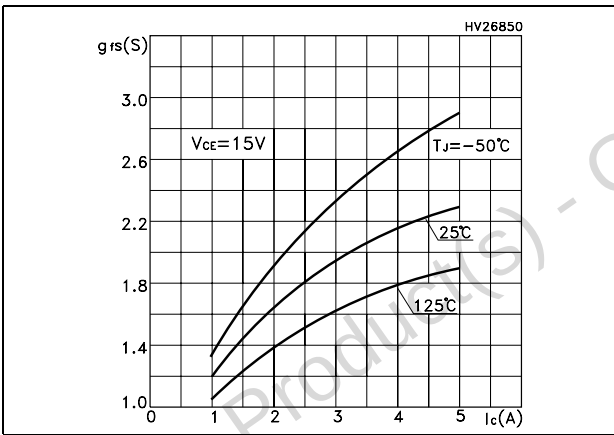


Figure 5. Collector-emitter on voltage vs temperature

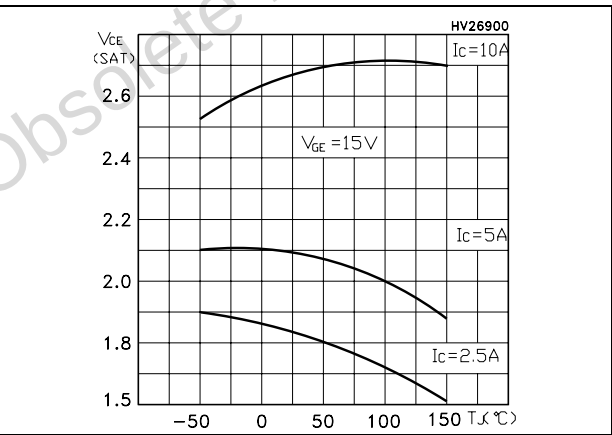


Figure 6. Gate charge vs gate-source voltage

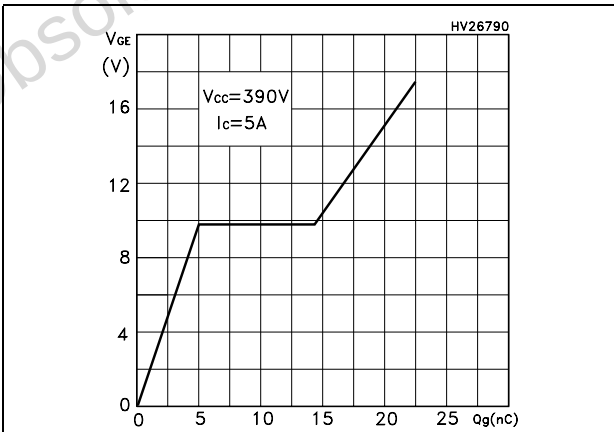


Figure 7. Capacitance variations

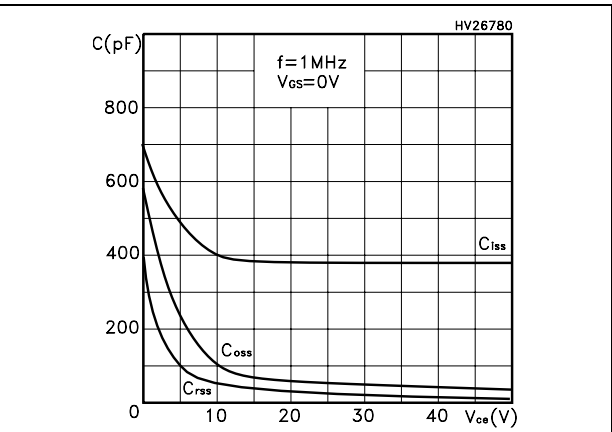


Figure 8. Normalized gate threshold voltage vs temperature

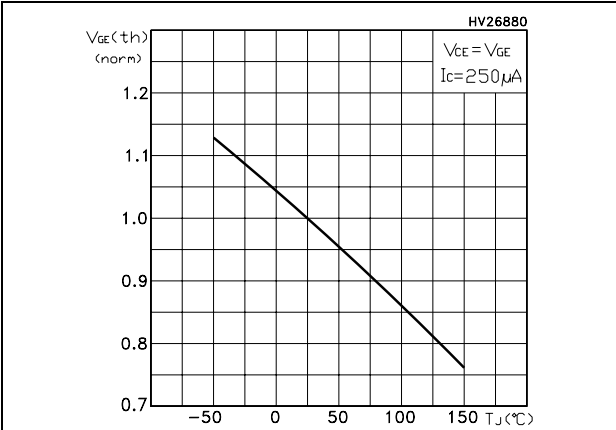


Figure 9. Collector-emitter on voltage vs collector current

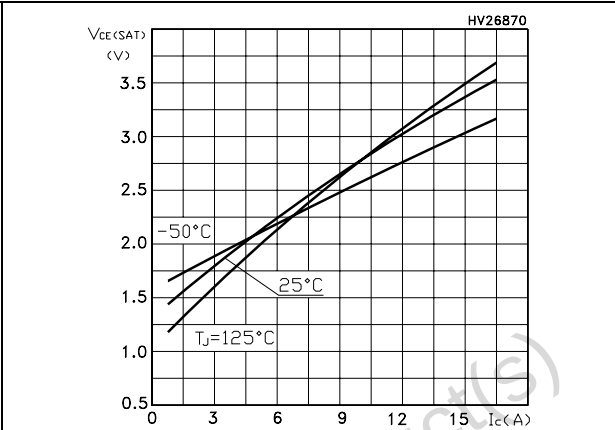


Figure 10. Normalized breakdown voltage vs temperature

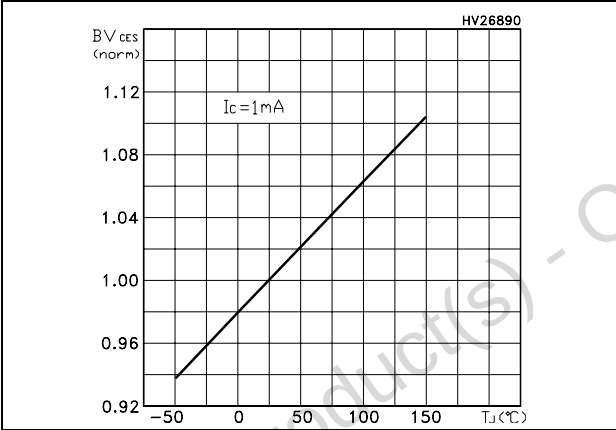


Figure 11. Switching losses vs temperature

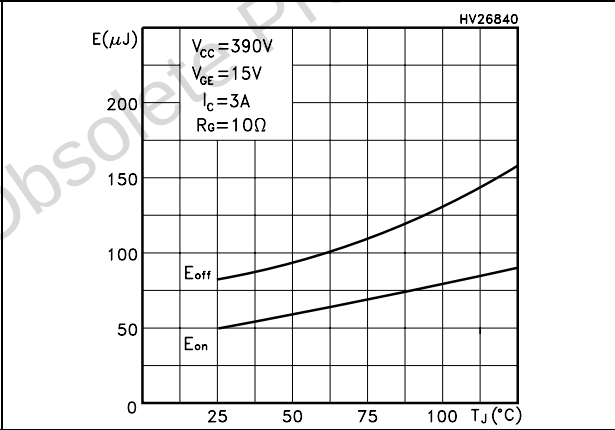


Figure 12. Switching losses vs gate resistance

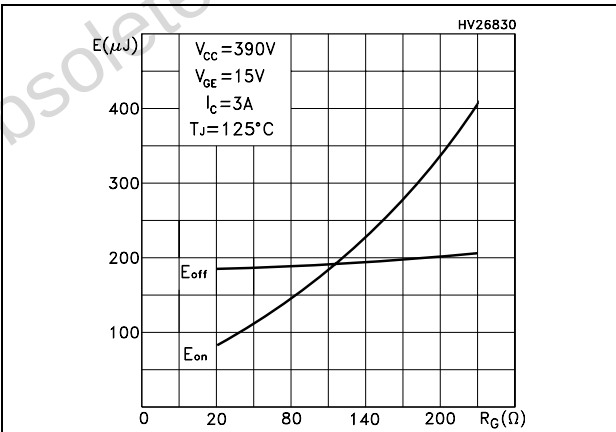


Figure 13. Switching losses vs collector current

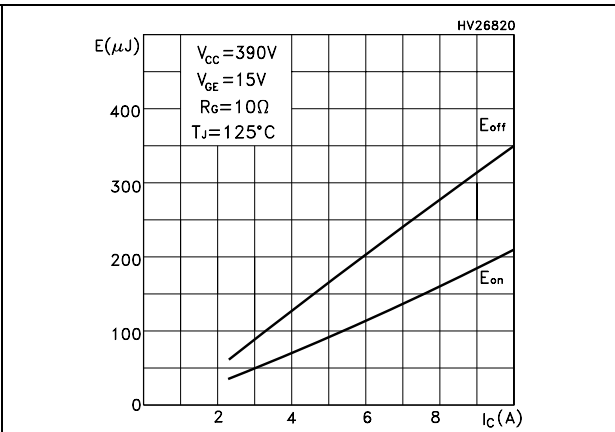


Figure 14. Thermal impedance for TO-220/
D²PAK

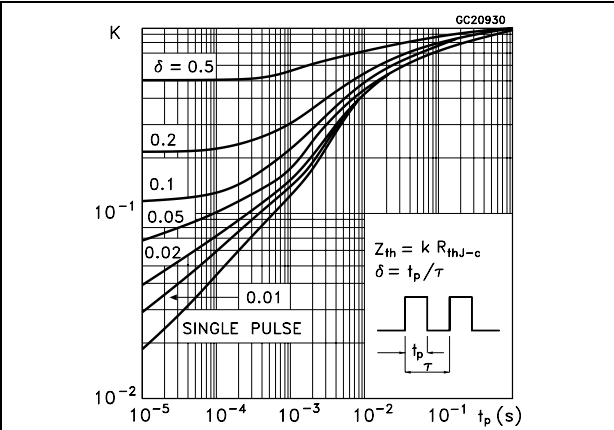


Figure 15. Turn-off SOA

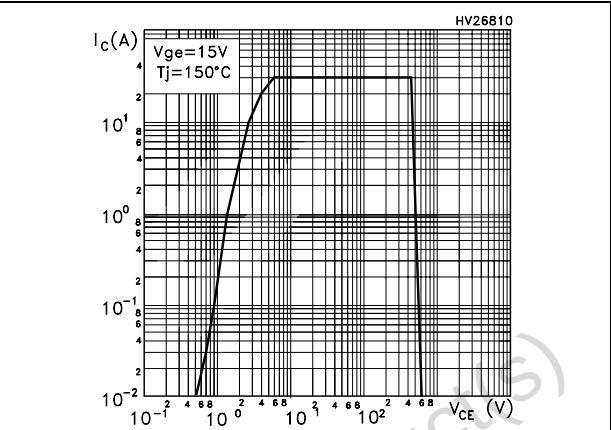
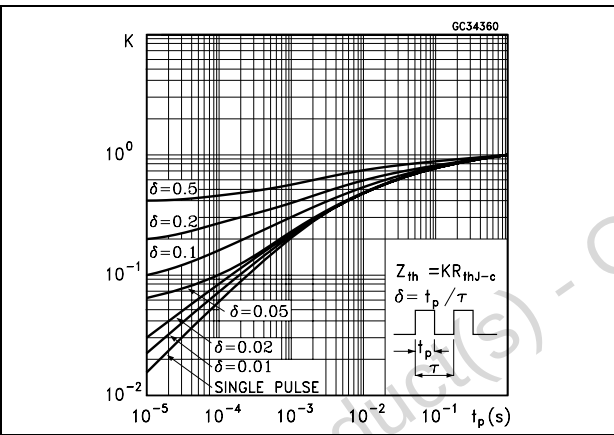


Figure 16. Thermal impedance for DPAK



3 Test circuit

Figure 17. Test circuit for inductive load switching

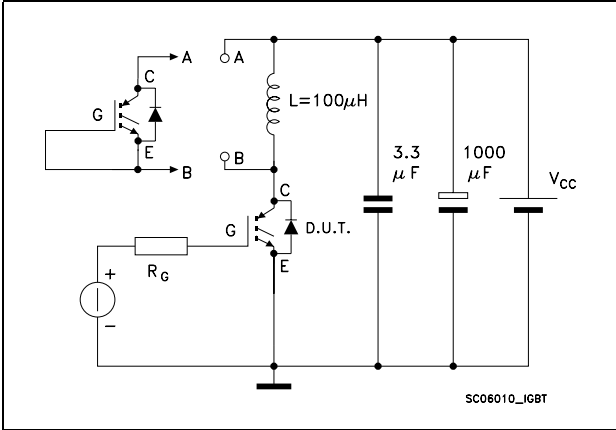


Figure 18. Gate charge test circuit

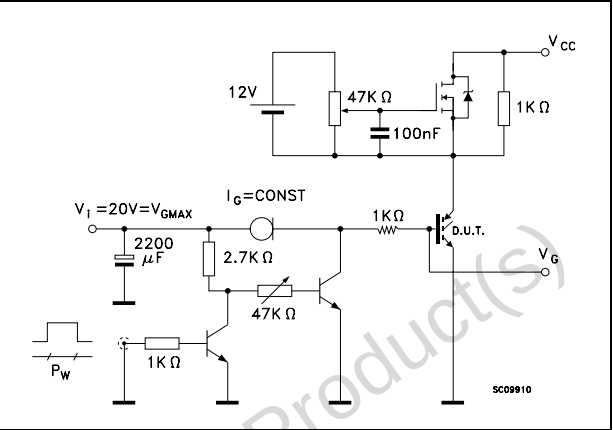


Figure 19. Switching waveform

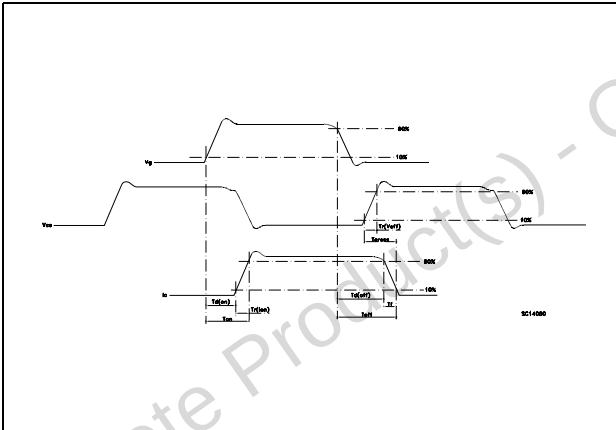
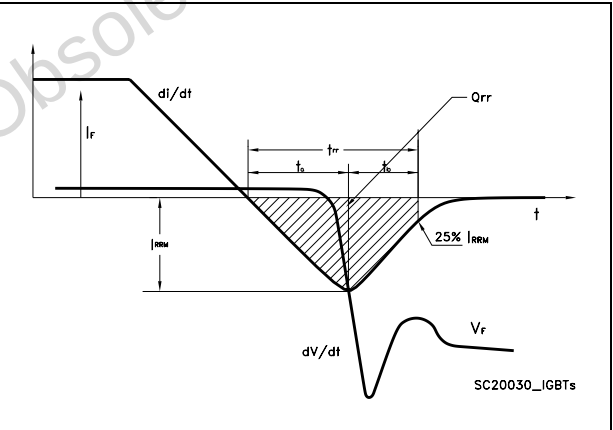


Figure 20. Diode recovery time waveform



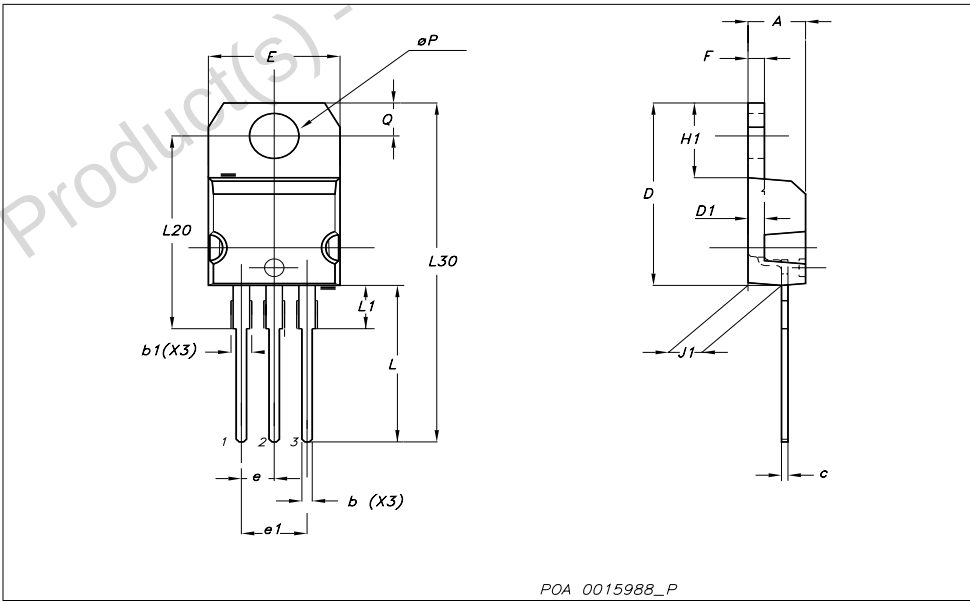
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Obsolete Product(s) - Obsolete Product(s)

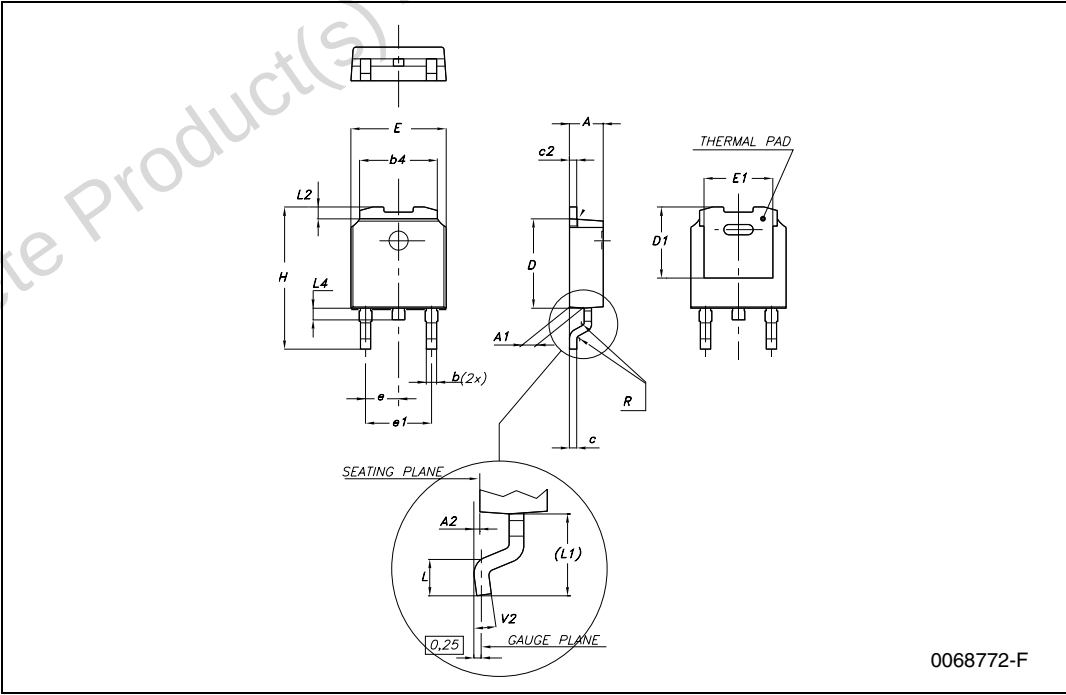
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



DPAK MECHANICAL DATA

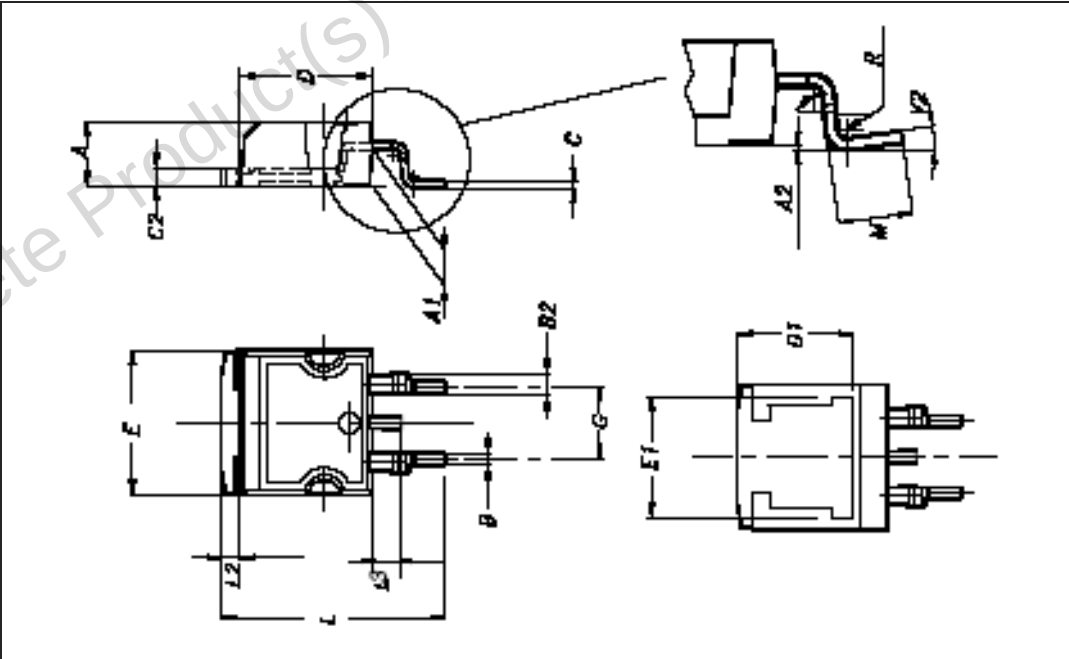
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
E	6.4		6.6	0.252		0.260
E1		4.7			0.185	
e		2.28			0.090	
e1	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°



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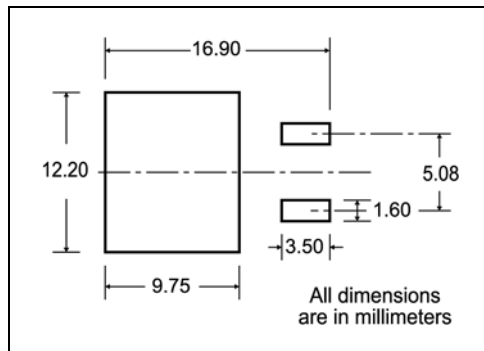
D²PAK mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		0.409
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.50		0.55
L3	1.4		1.75	0.055		0.68
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			

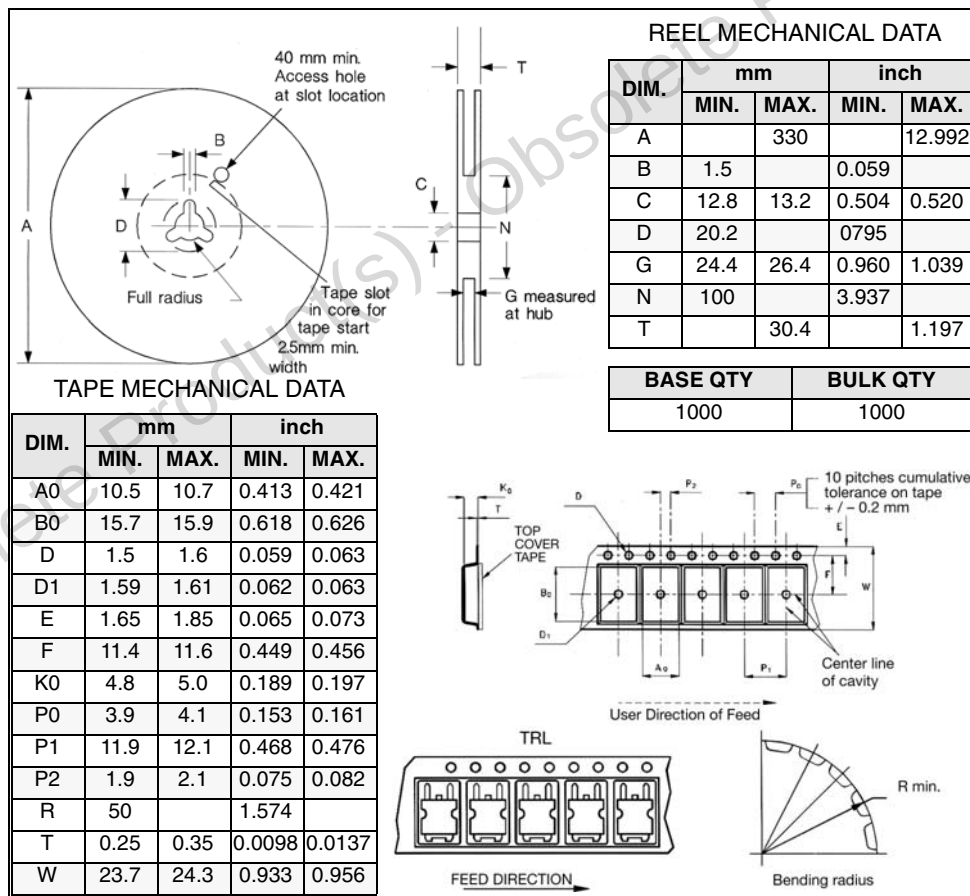


5 Packaging mechanical data

D²PAK FOOTPRINT

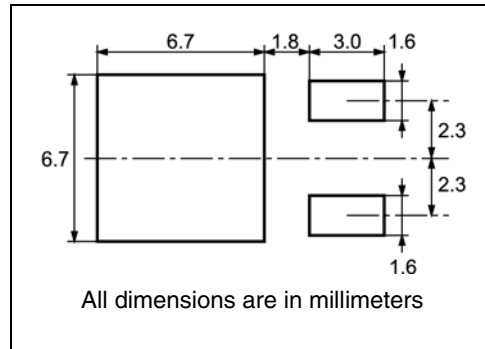


TAPE AND REEL SHIPMENT

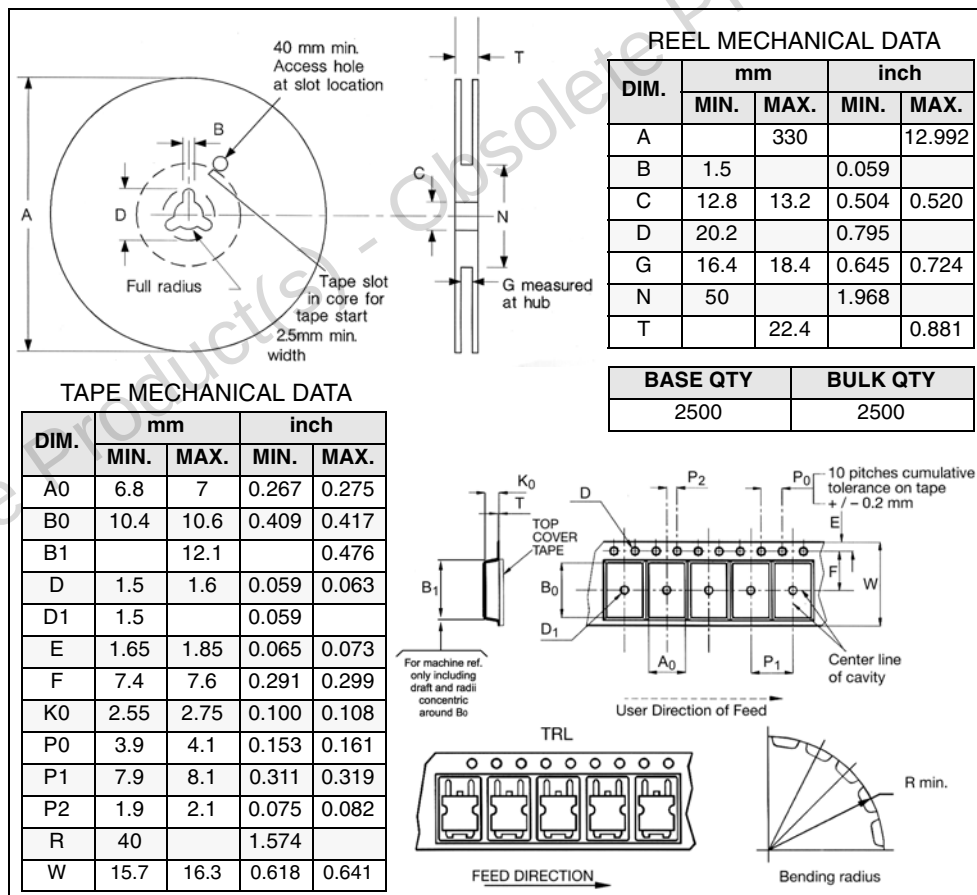


* on sales type

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT



6 Revision history

Table 8. Document revision history

Date	Revision	Changes
02-Oct-2007	1	First release

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